

FIG.1

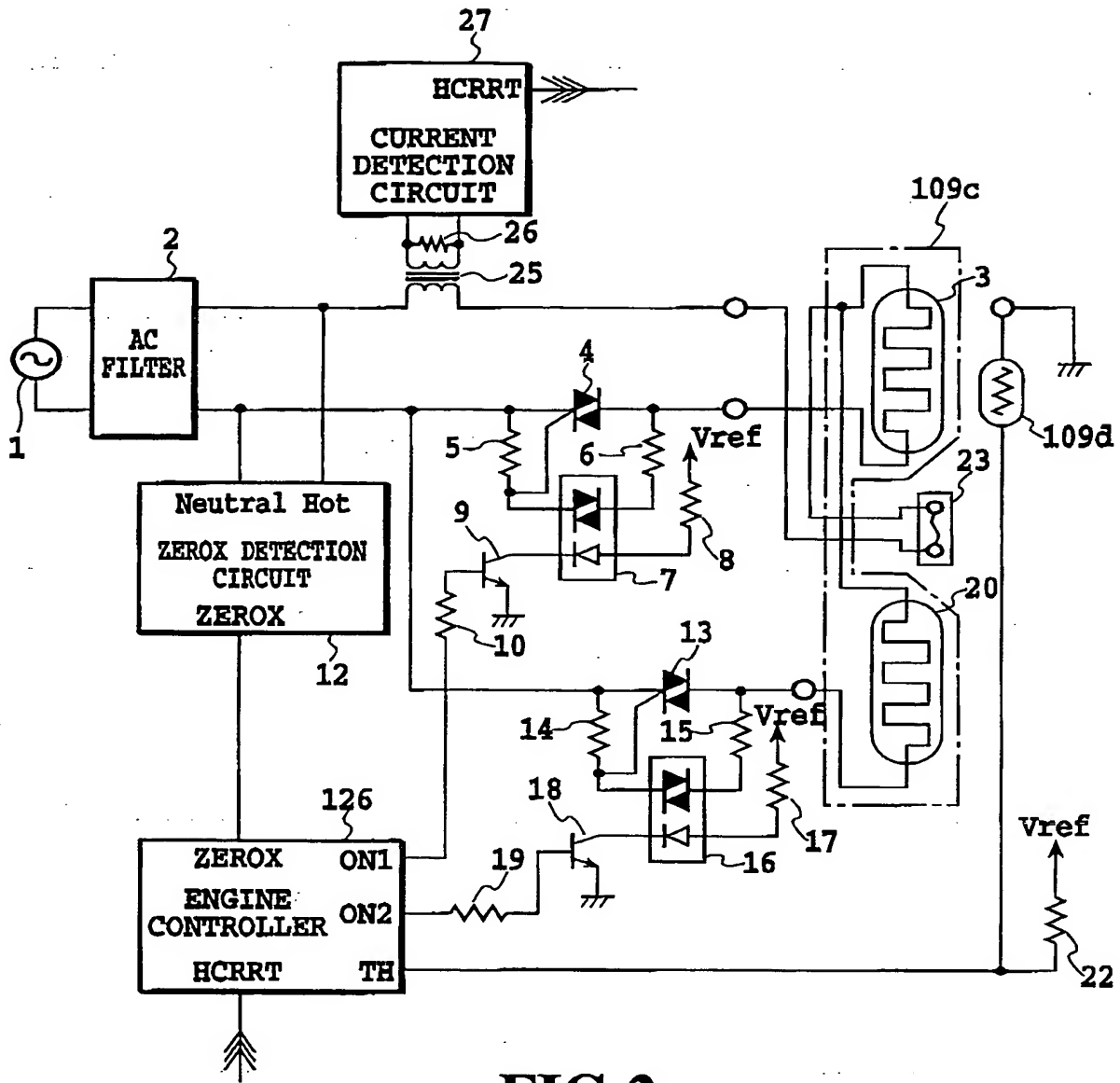


FIG.2

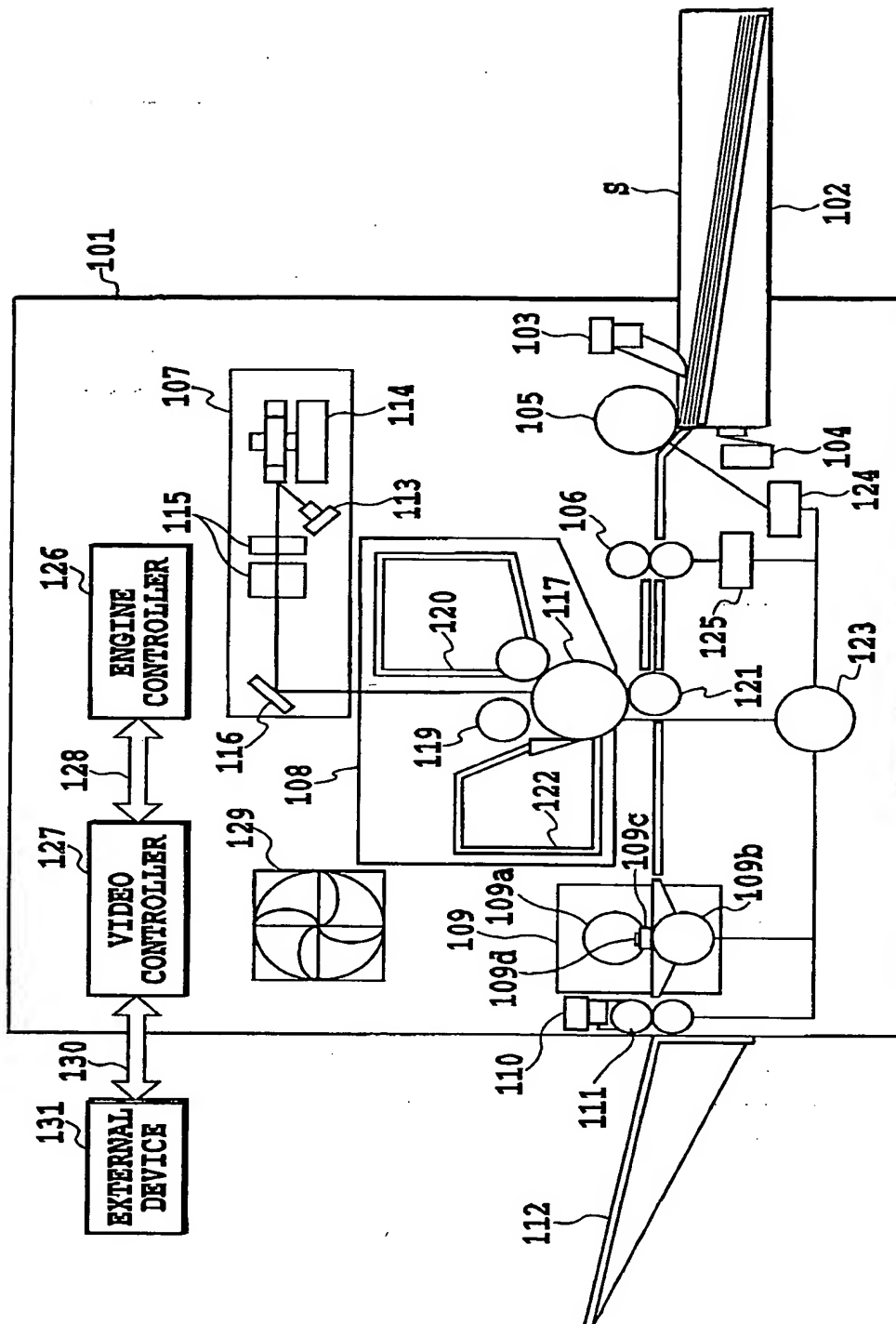


FIG. 3

FIG.4A

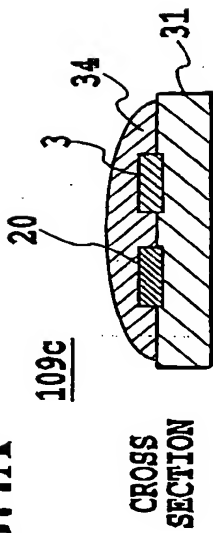
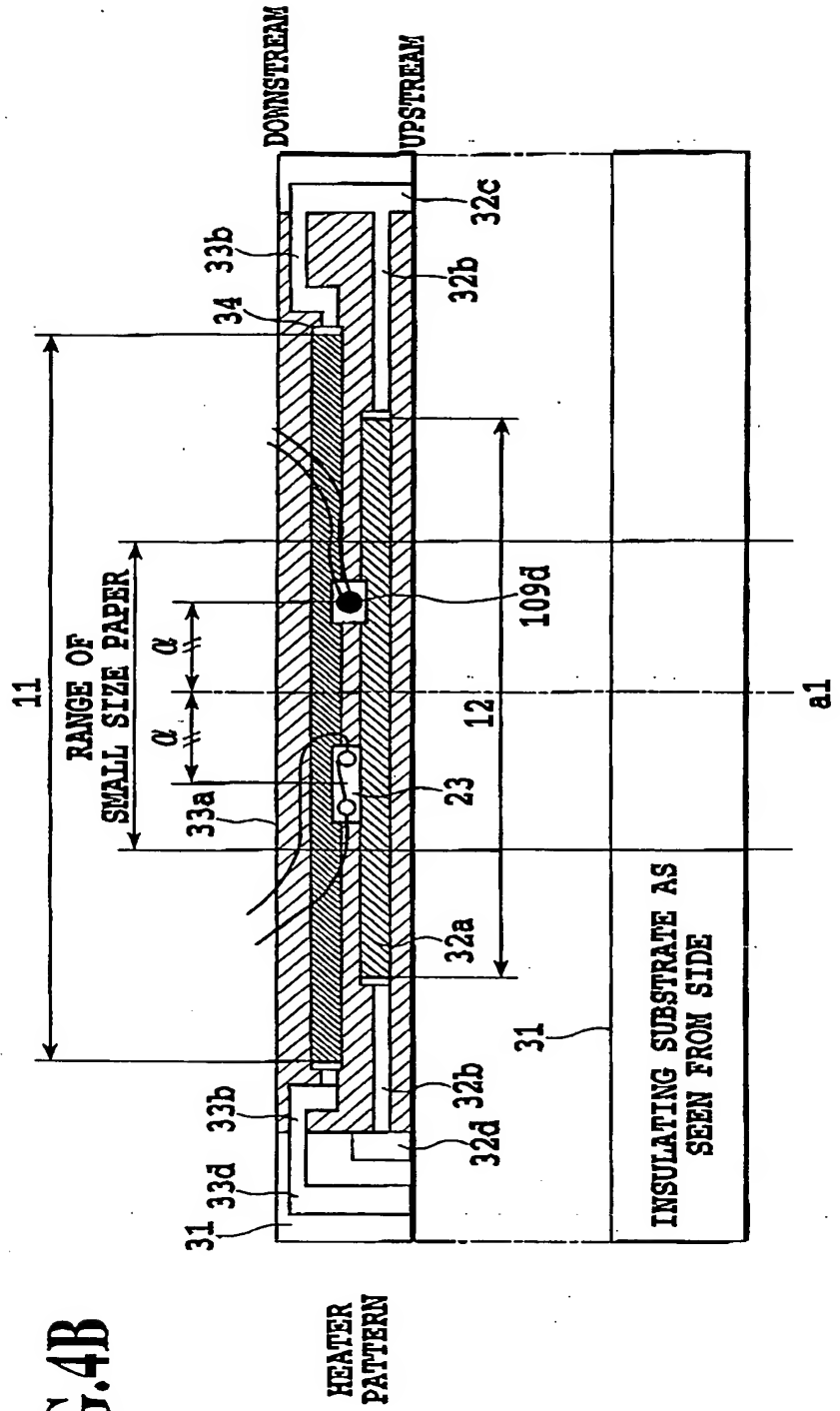


FIG.4B



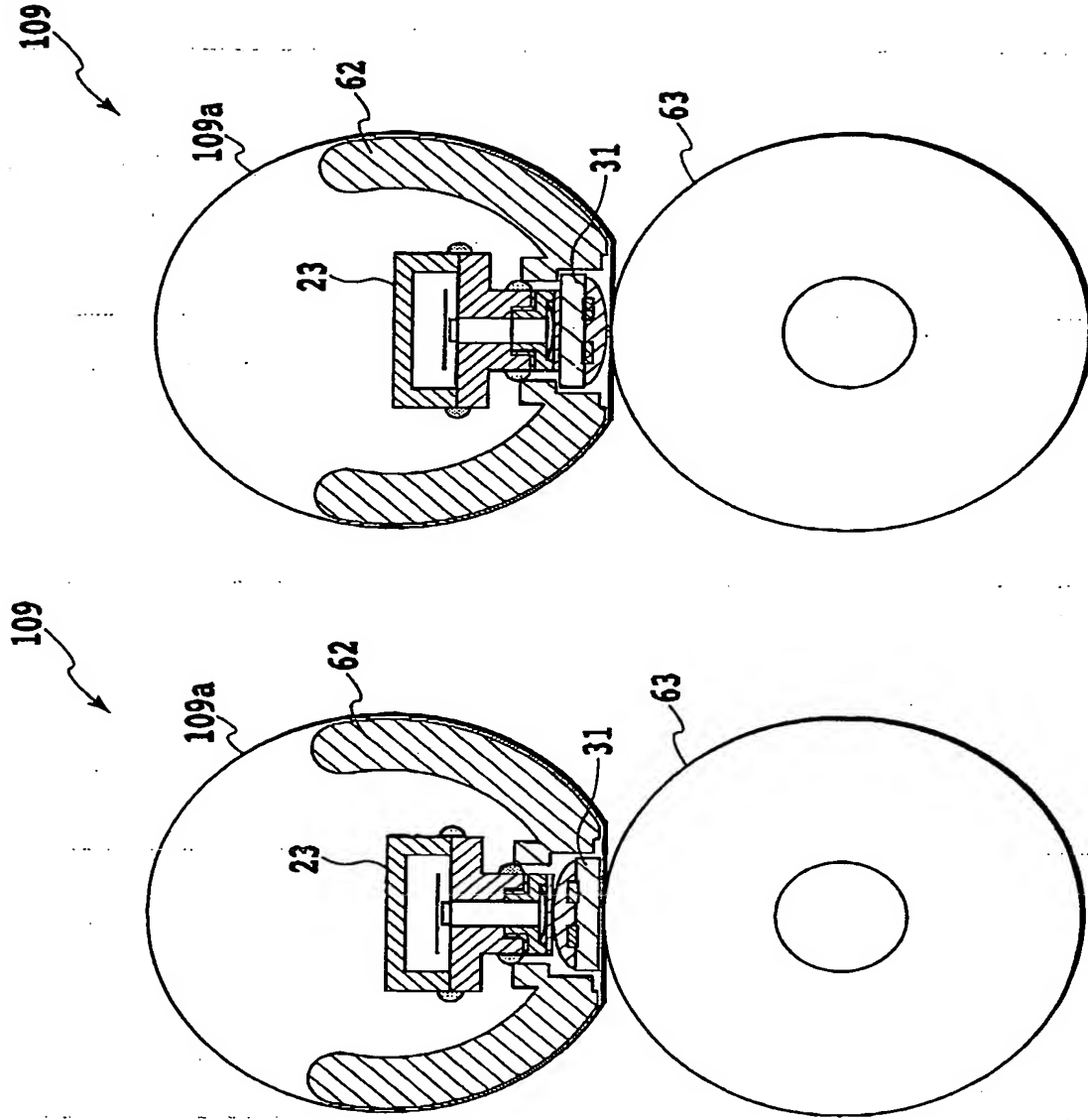


FIG.5B

FIG.5A

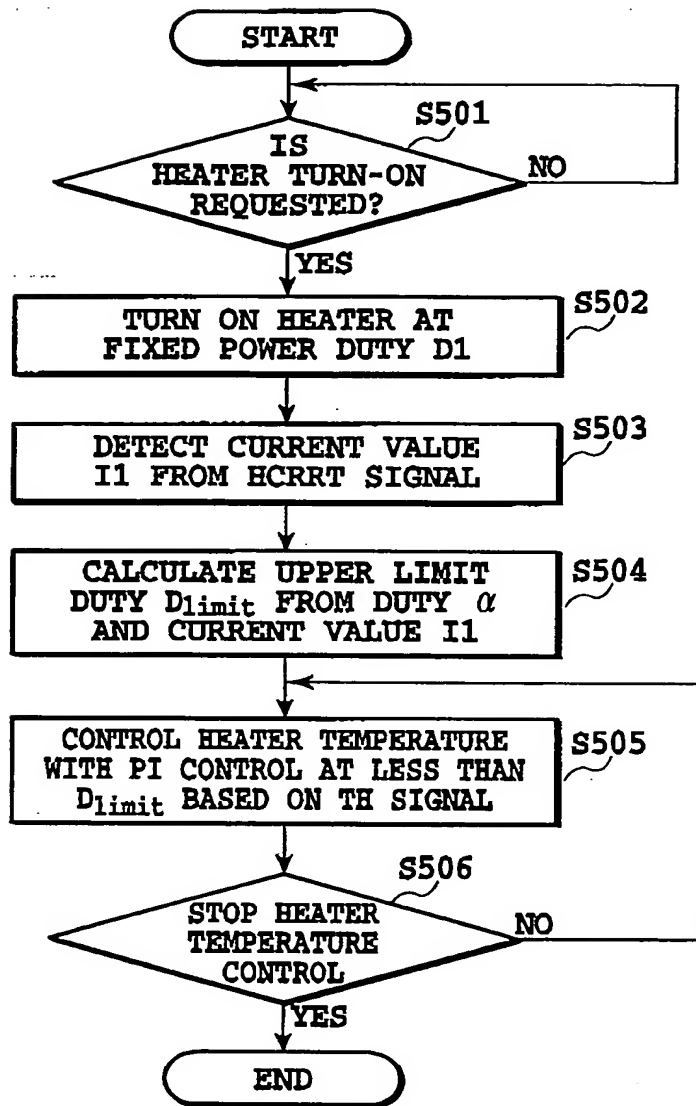


FIG.6

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WHEN FIXED DUTY D1 IS SUPPLIED

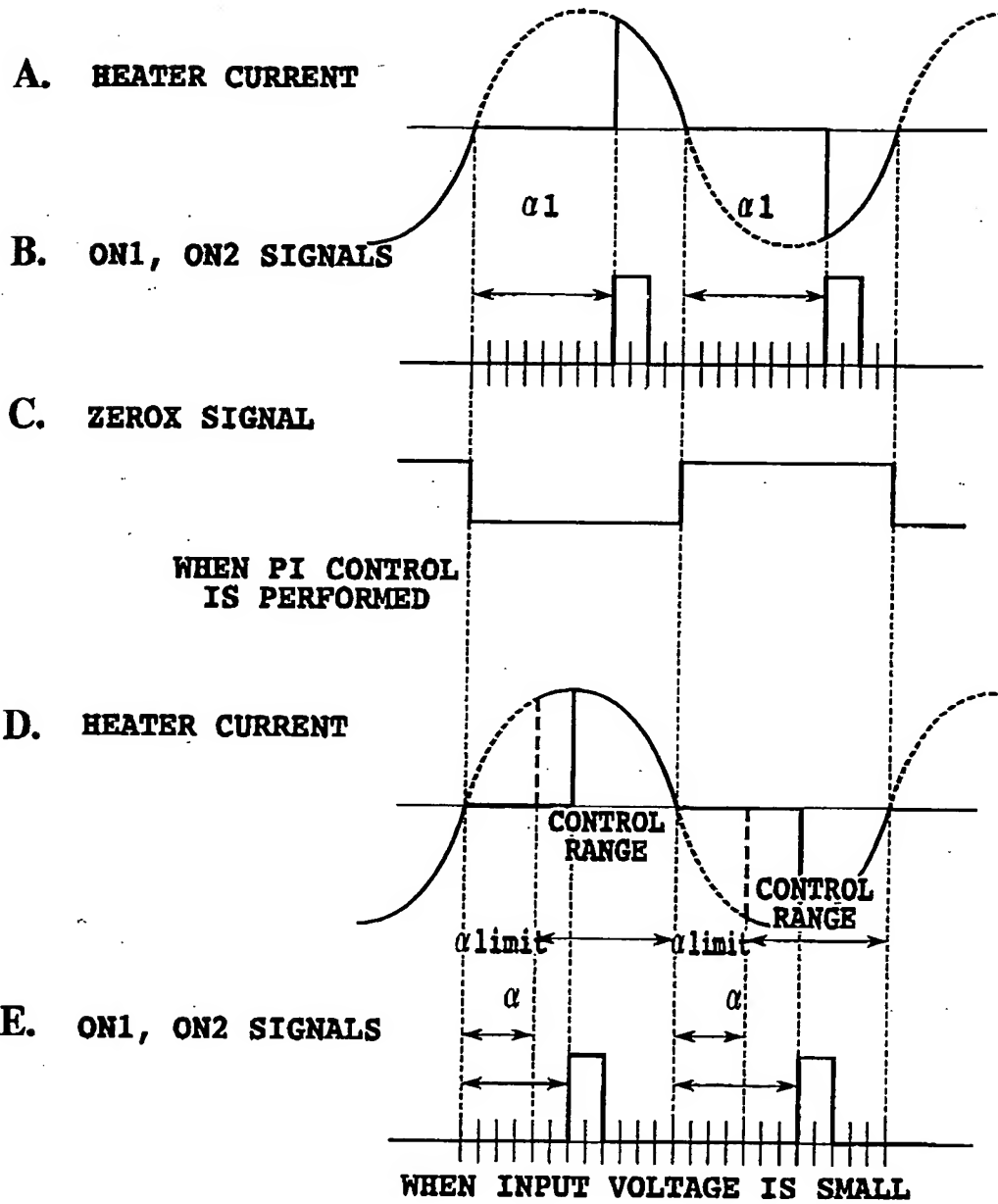


FIG.7

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WHEN FIXED DUTY D1 IS SUPPLIED

A. HEATER CURRENT

B. ON1, ON2 SIGNALS

C. ZEROX SIGNAL

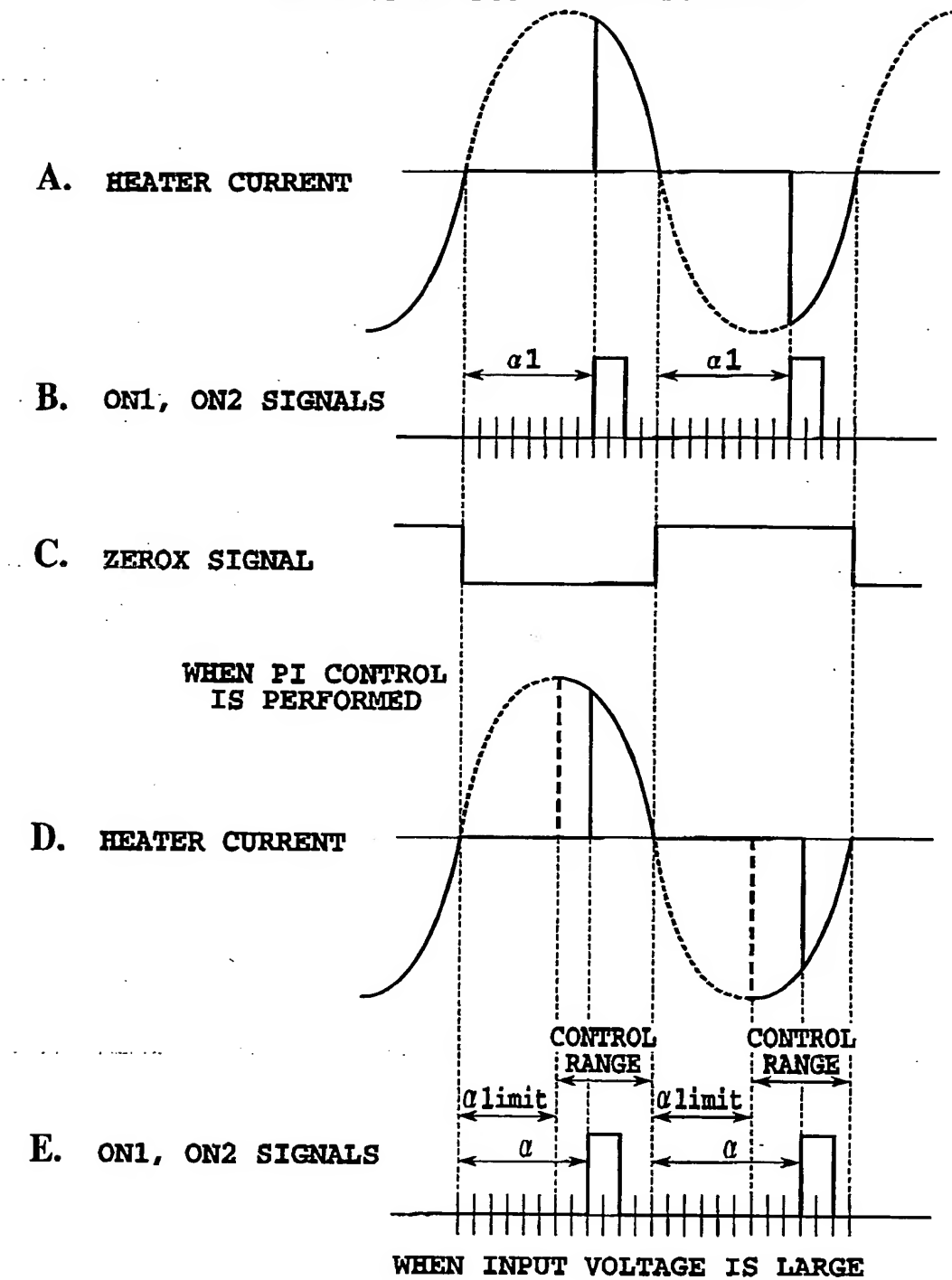
WHEN PI CONTROL
IS PERFORMED

D. HEATER CURRENT

E. ON1, ON2 SIGNALS

WHEN INPUT VOLTAGE IS LARGE

FIG.8



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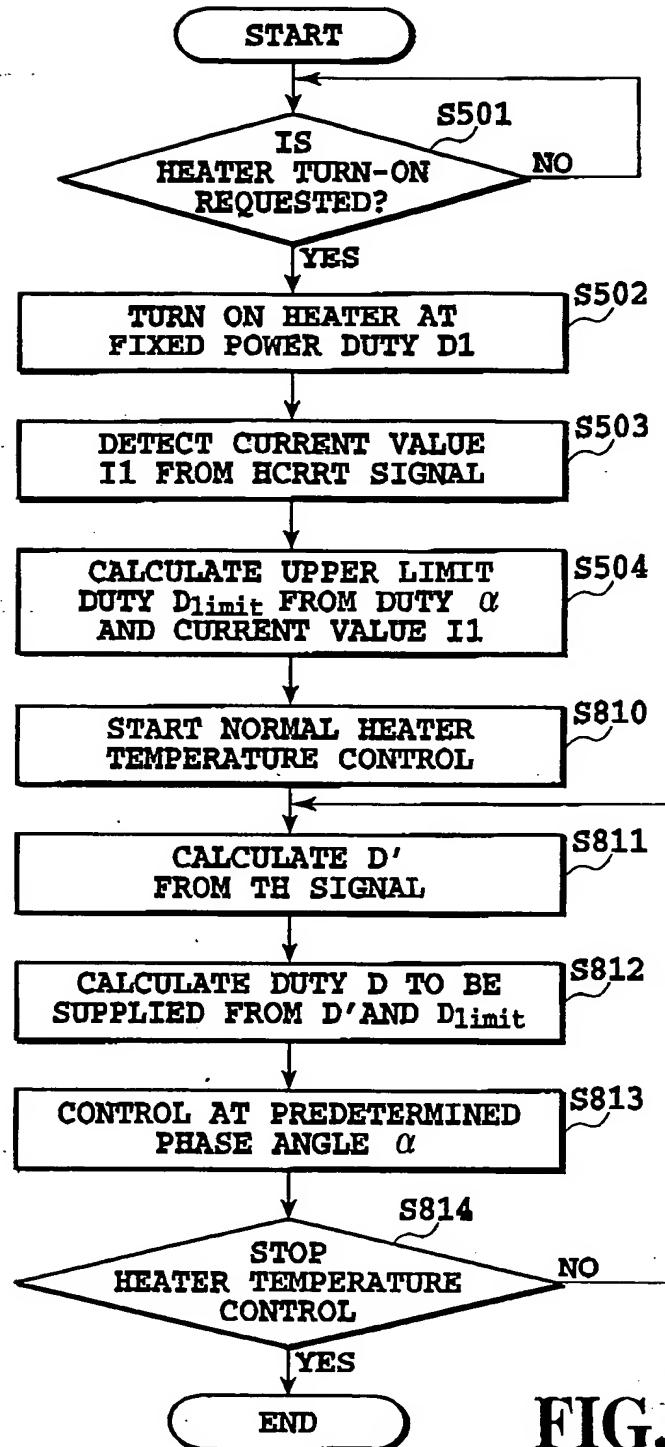
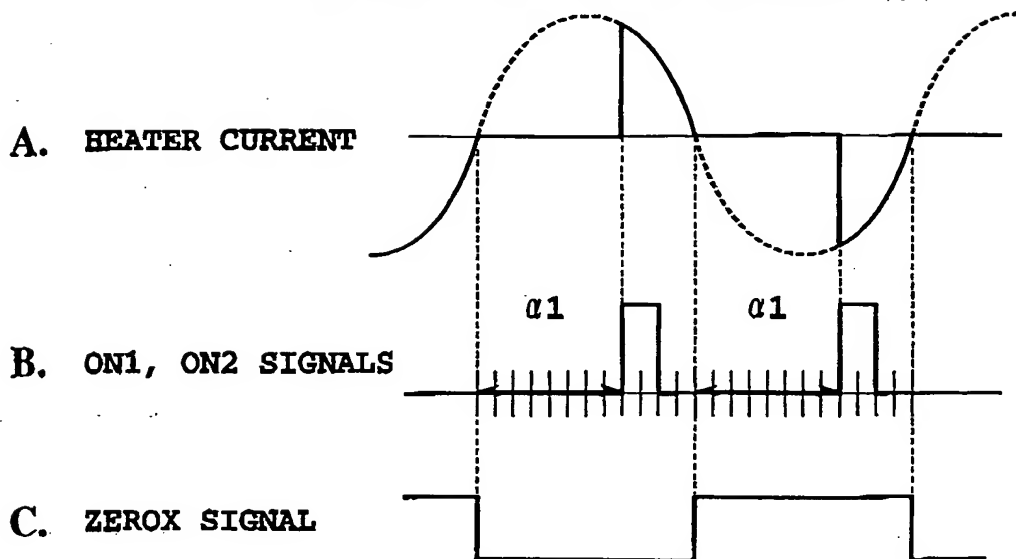


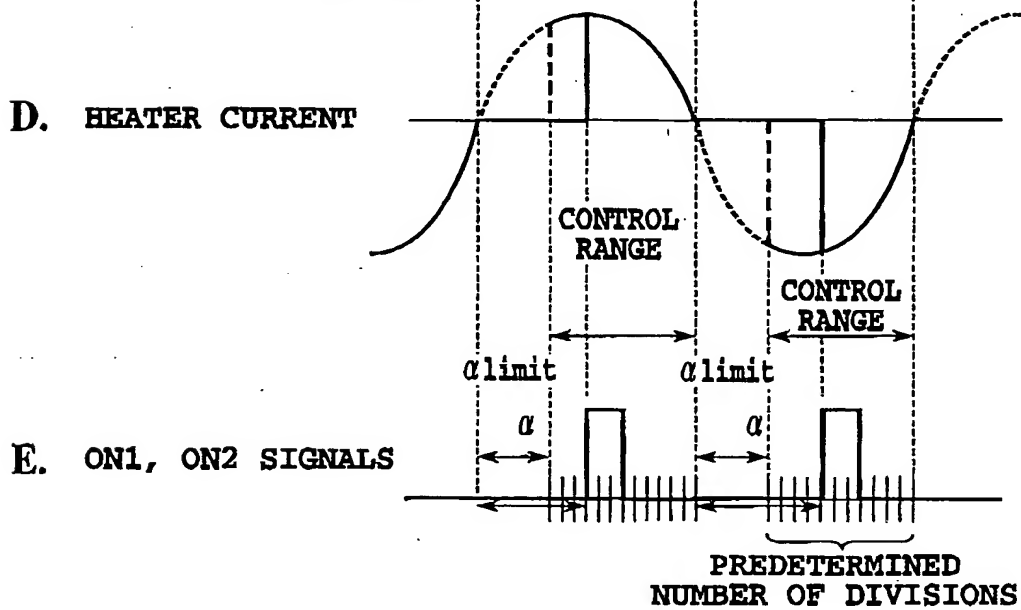
FIG.9

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WHEN FIXED DUTY D1 IS SUPPLIED



WHEN PI CONTROL
IS PERFORMED



WHEN INPUT VOLTAGE IS SMALL

FIG.10

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WHEN FIXED DUTY D1 IS SUPPLIED

A. HEATER CURRENT

B. ON1, ON2 SIGNALS

C. ZEROX SIGNAL

WHEN PI CONTROL
IS PERFORMED

D. HEATER CURRENT

E. ON1, ON2 SIGNALS

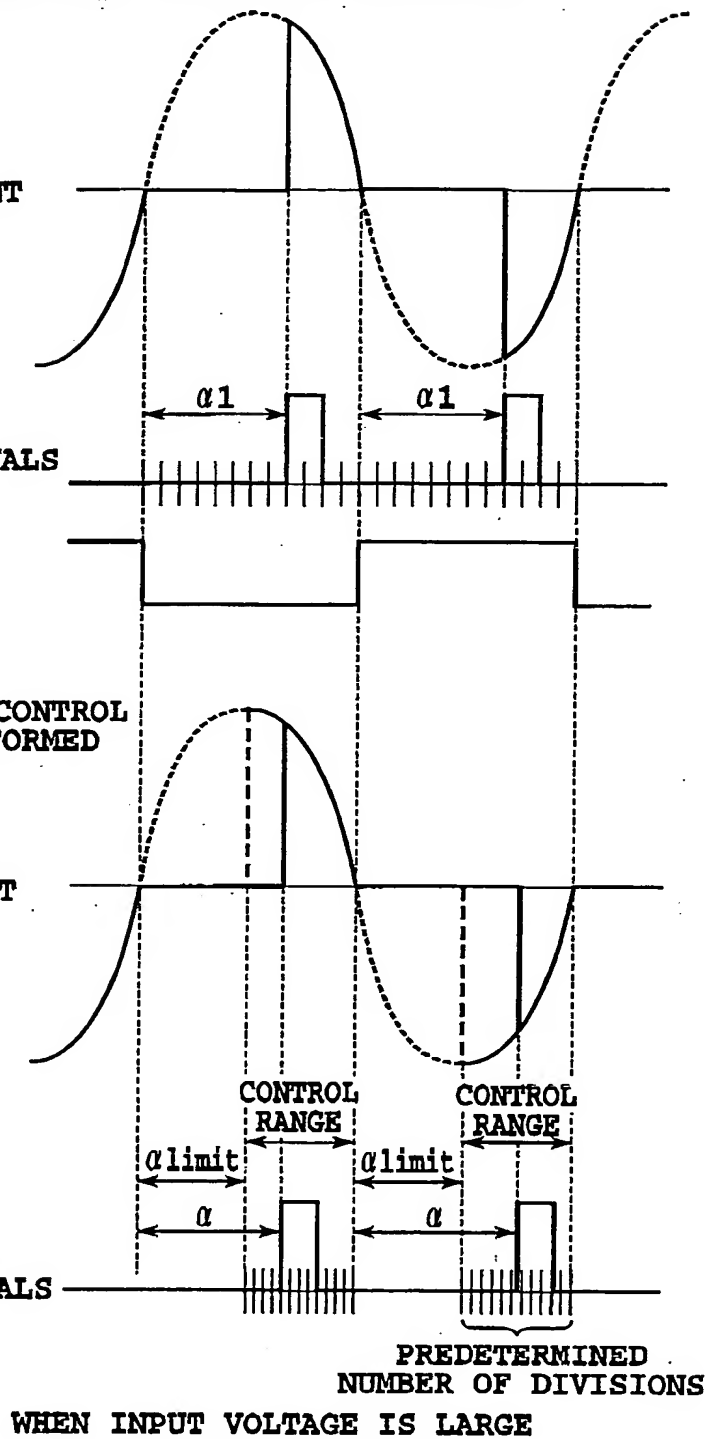


FIG.11

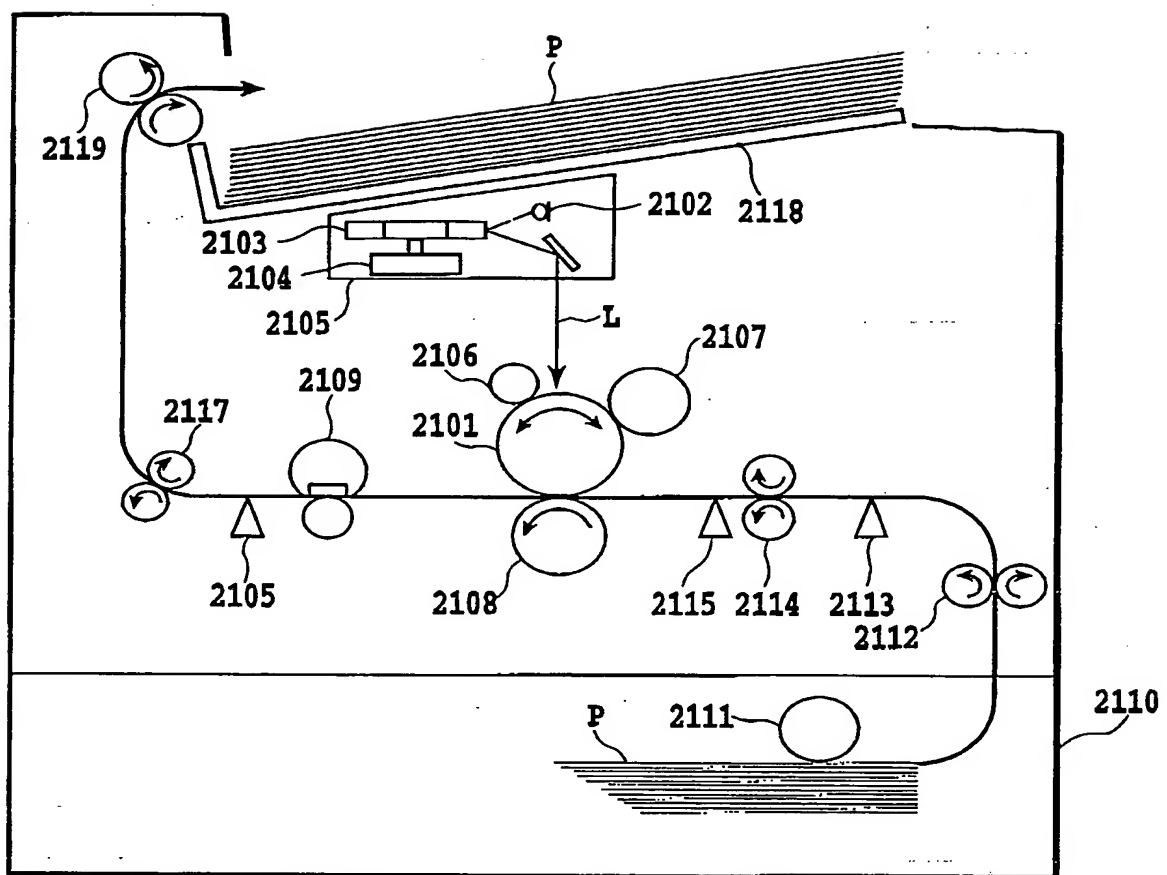


FIG.12

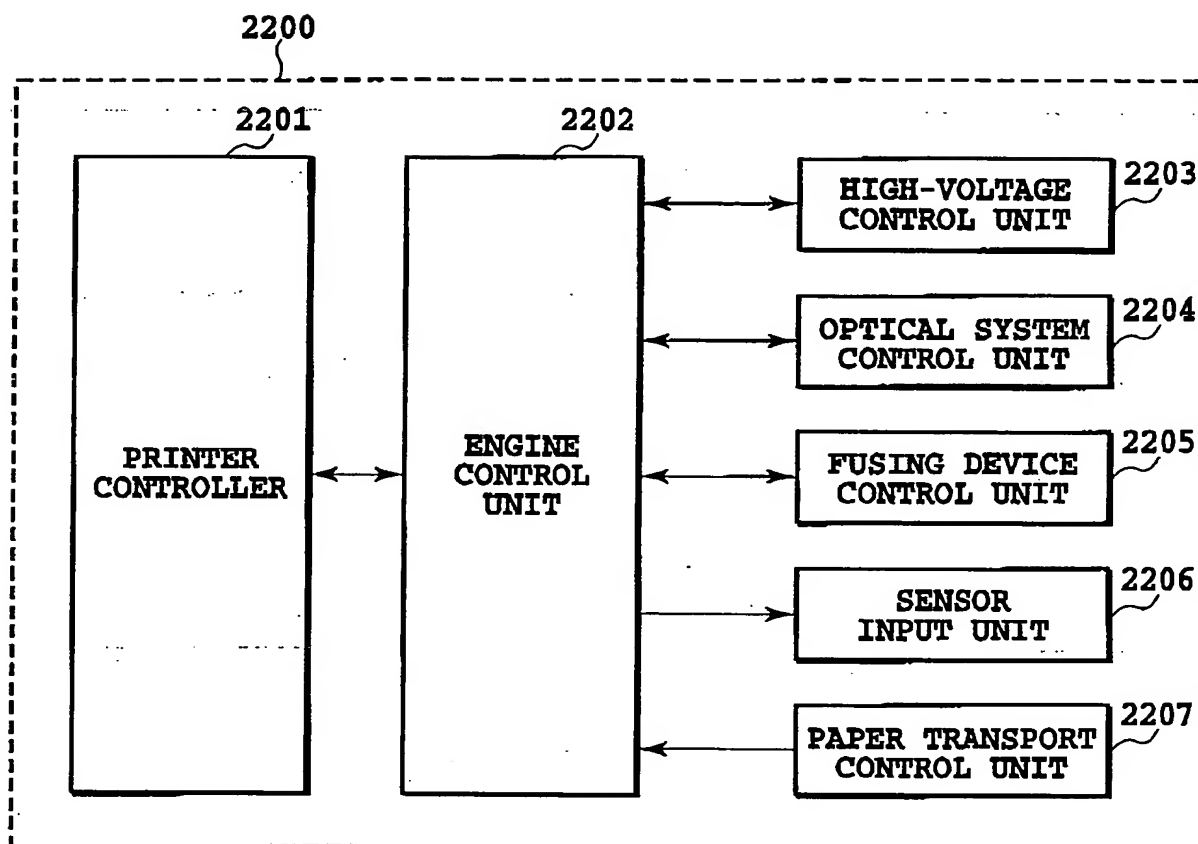


FIG.13

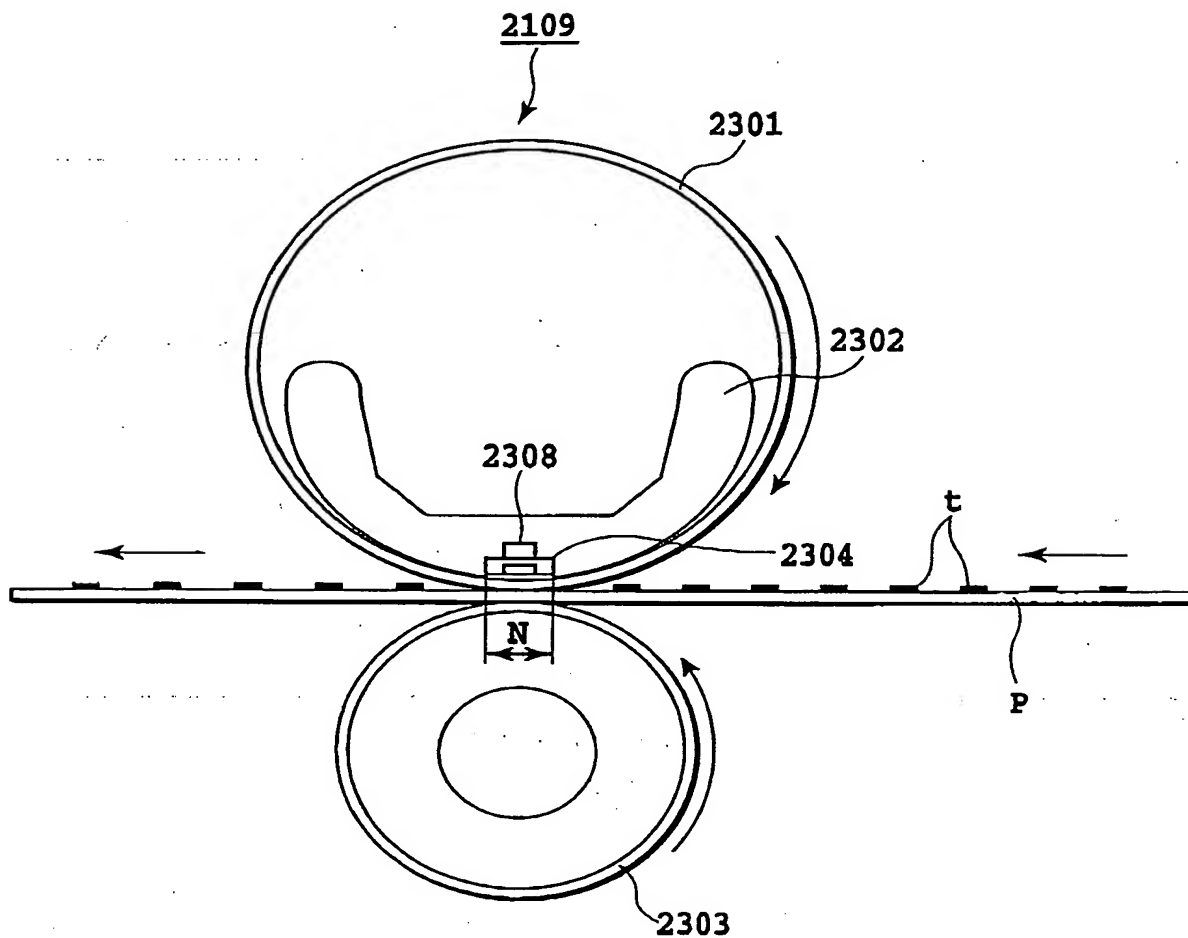


FIG.14

HEATER BACK
SURFACE SIDE

2308

2304a

This diagram shows the top view of the heater back surface side. It features a rectangular area labeled 2308, which is a central component. To the right of this area is a larger rectangular region labeled 2304a. A small rectangular feature is located at the bottom center of the 2308 area.

A cross-sectional view of a semiconductor device 2304. The device consists of a substrate 2306 with a top surface 2307. A layer 2308 is formed on the top surface 2307. A side surface 2304a is shown on the right side of the device.

FIG.15C

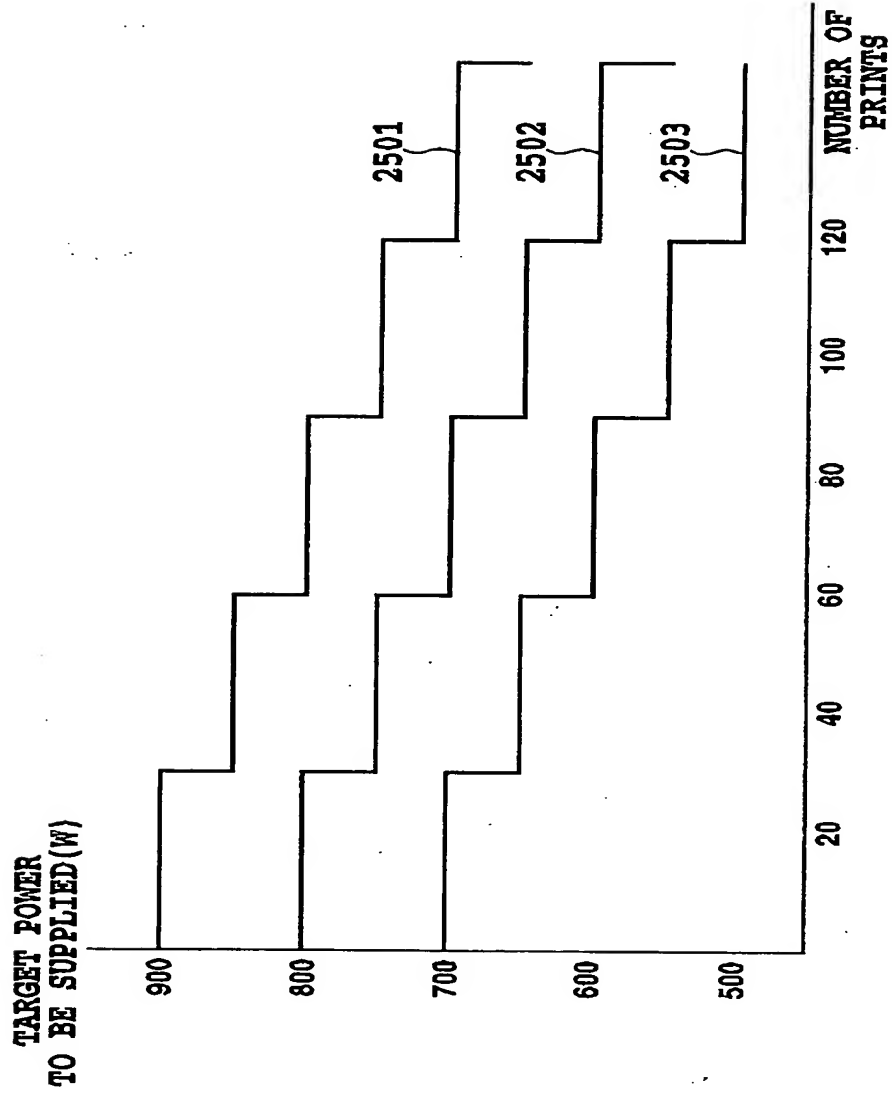


FIG.16

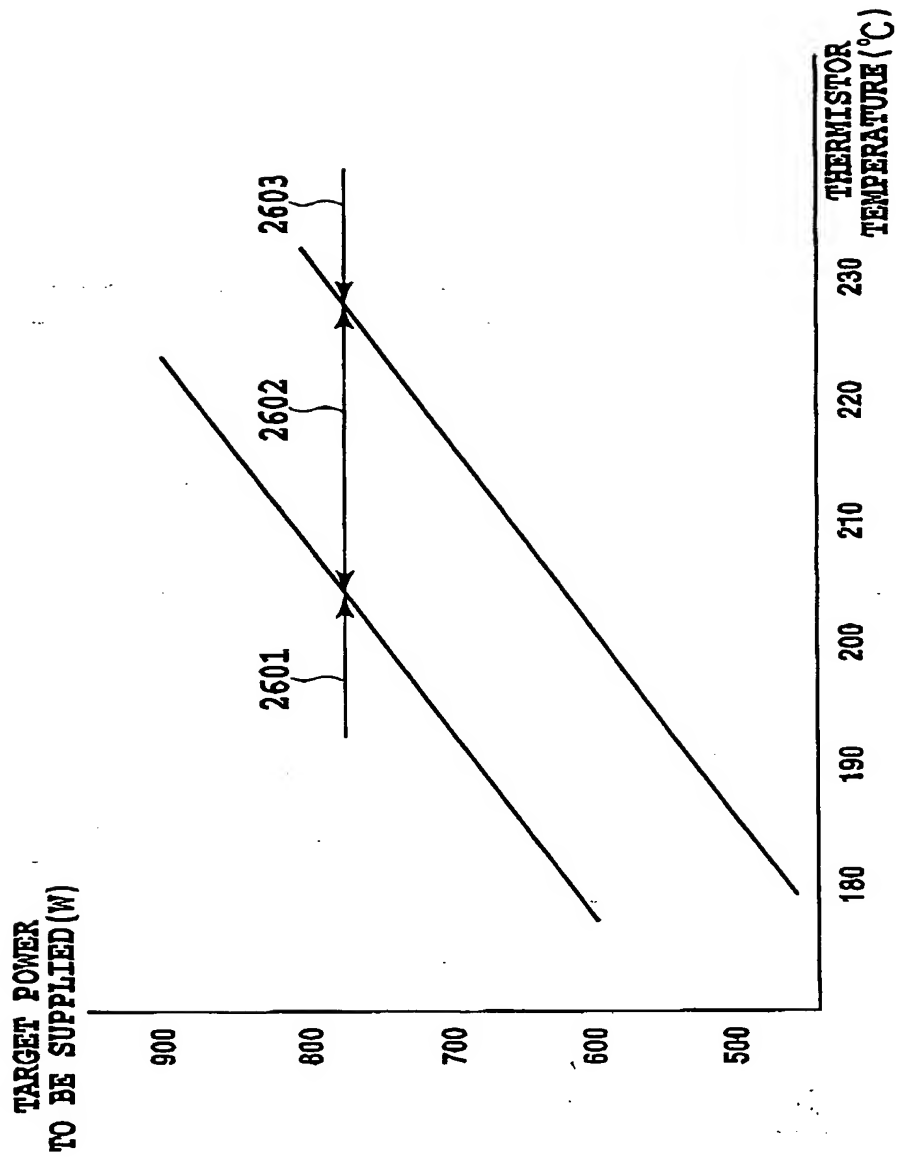


FIG.17

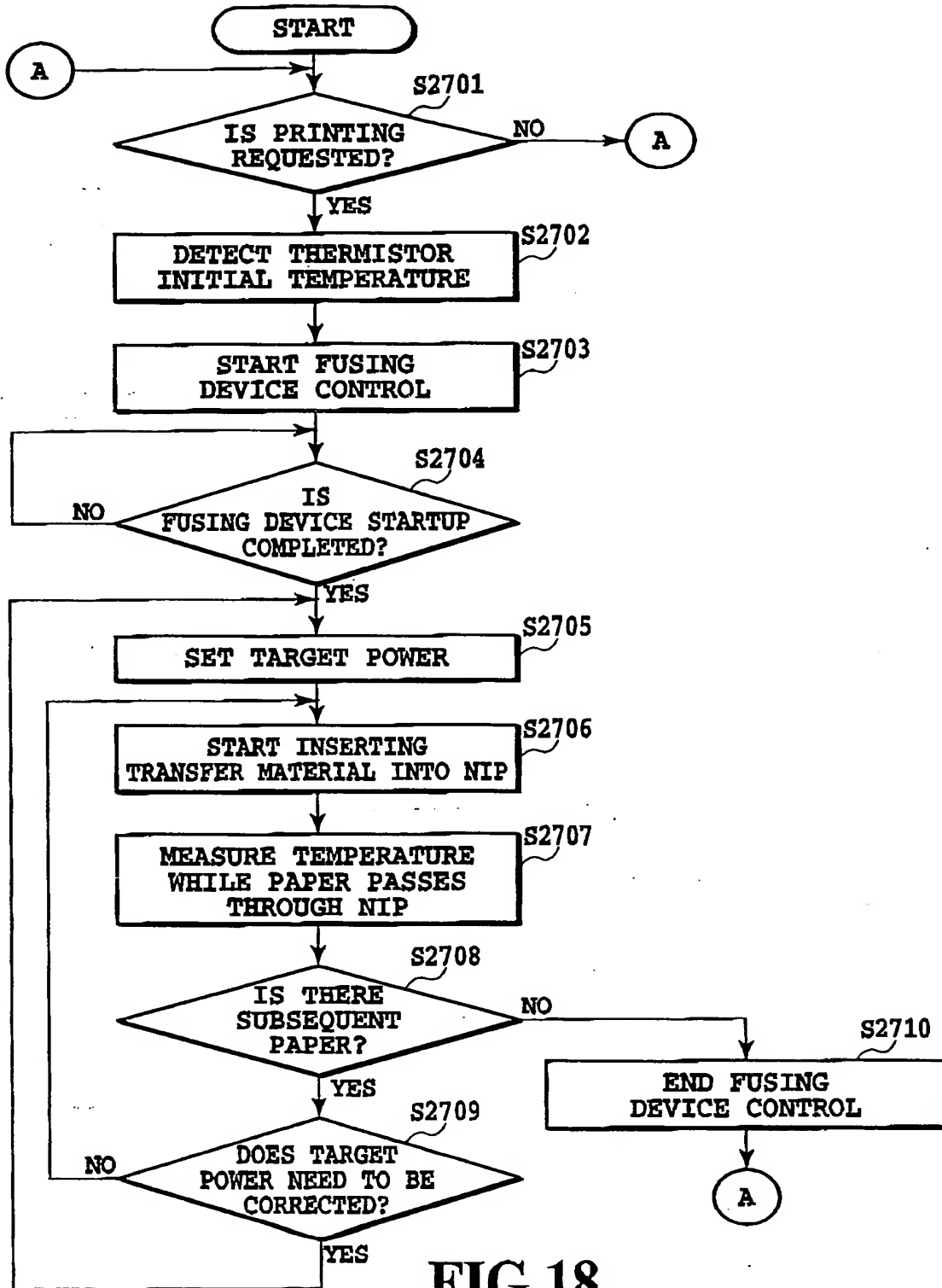


FIG.18

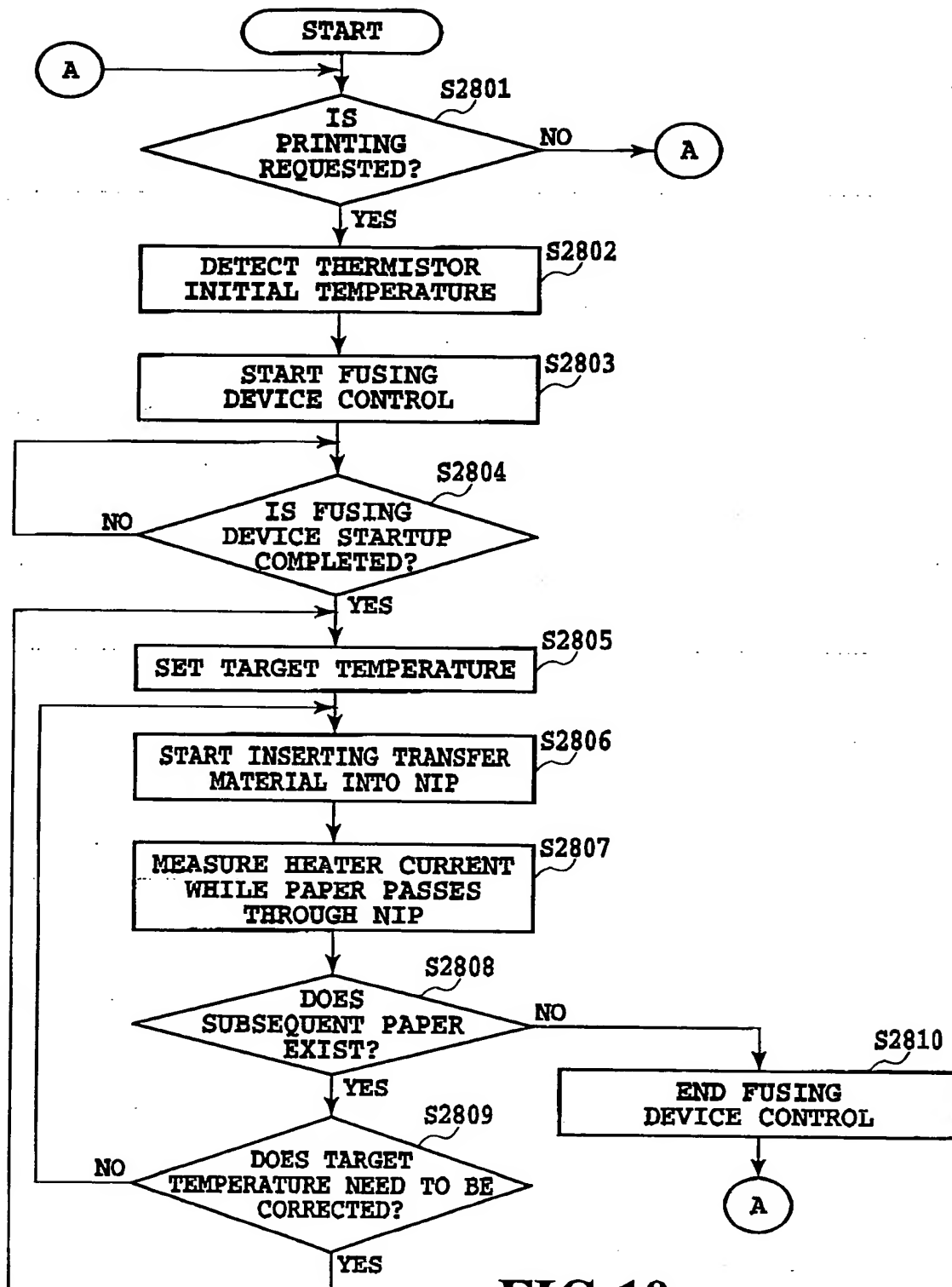


FIG.19

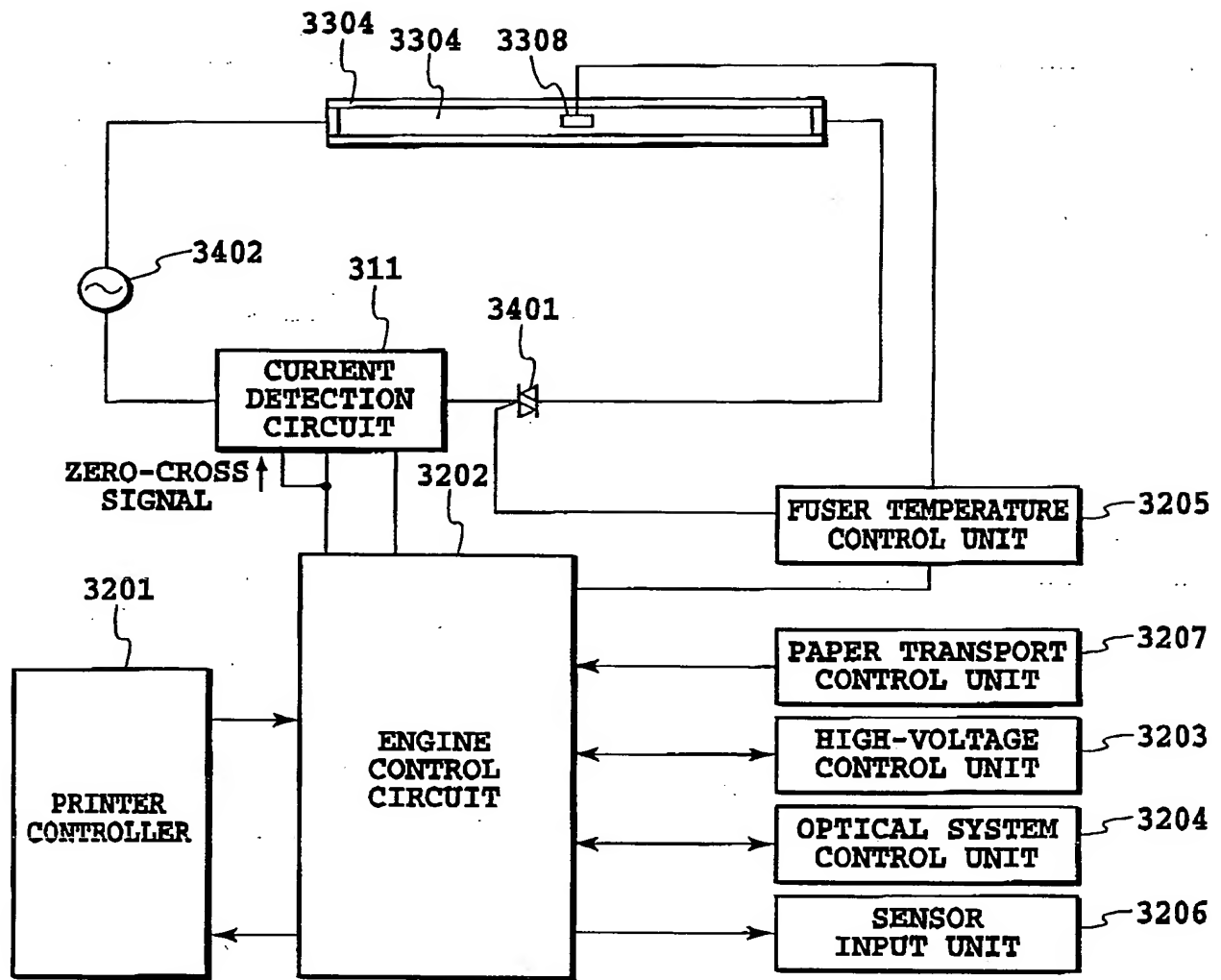


FIG.20

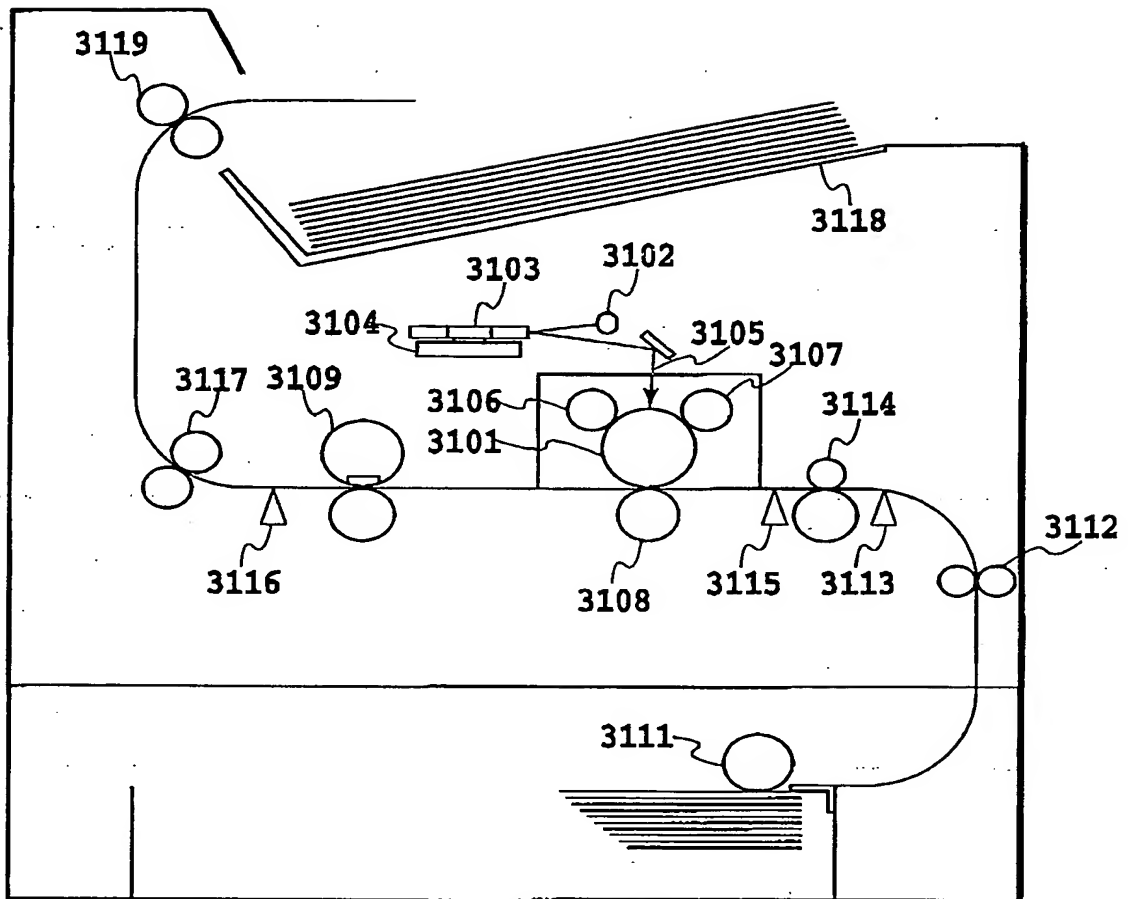


FIG.21

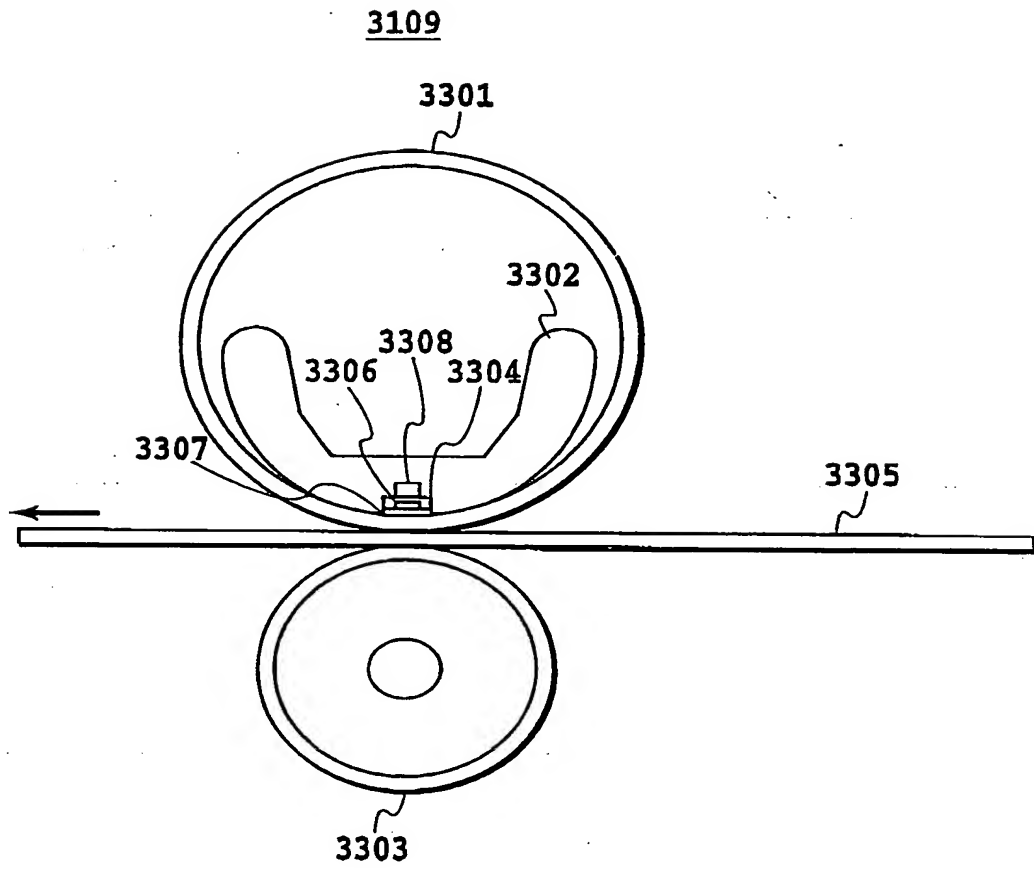


FIG.22

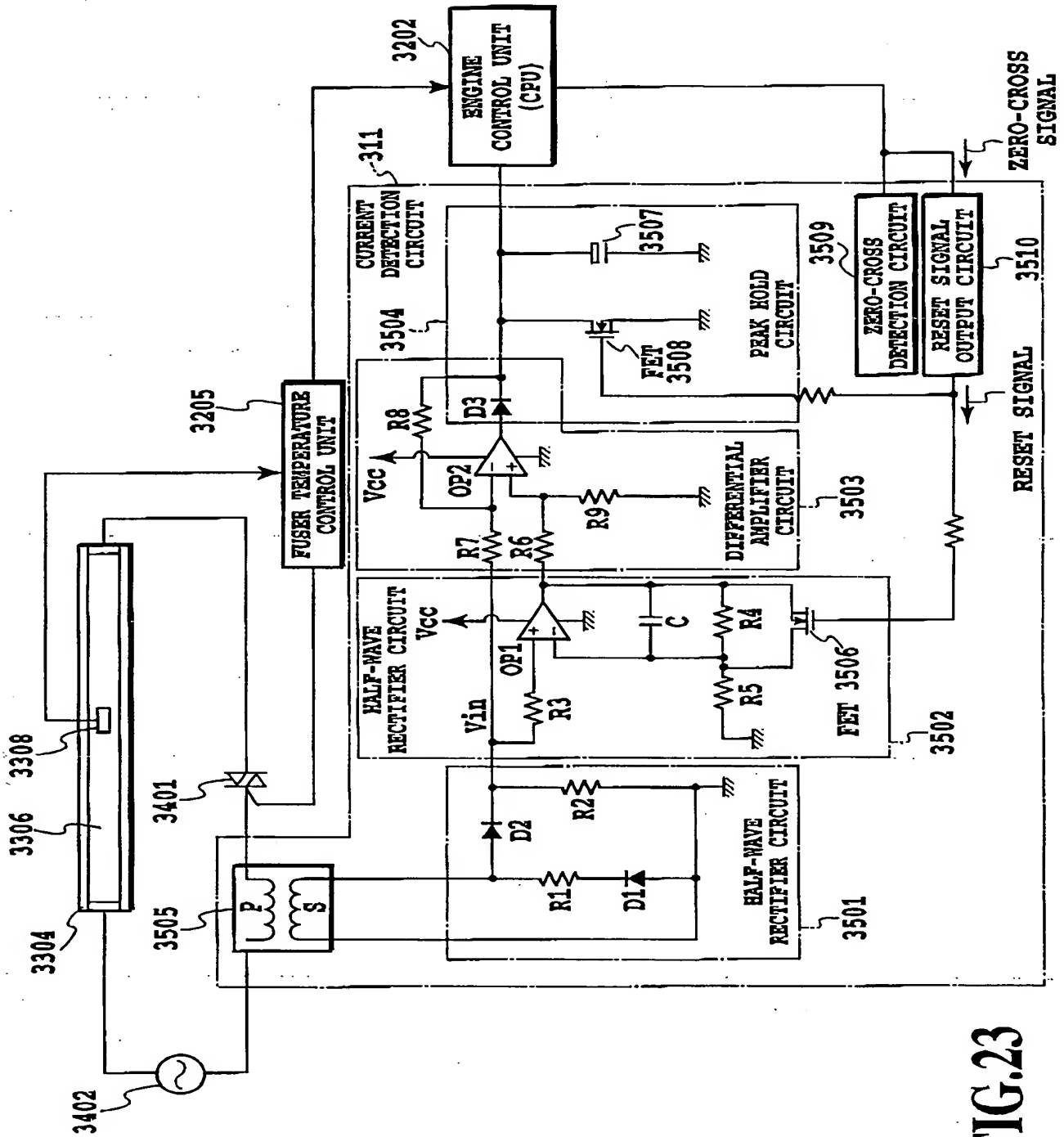


FIG.23

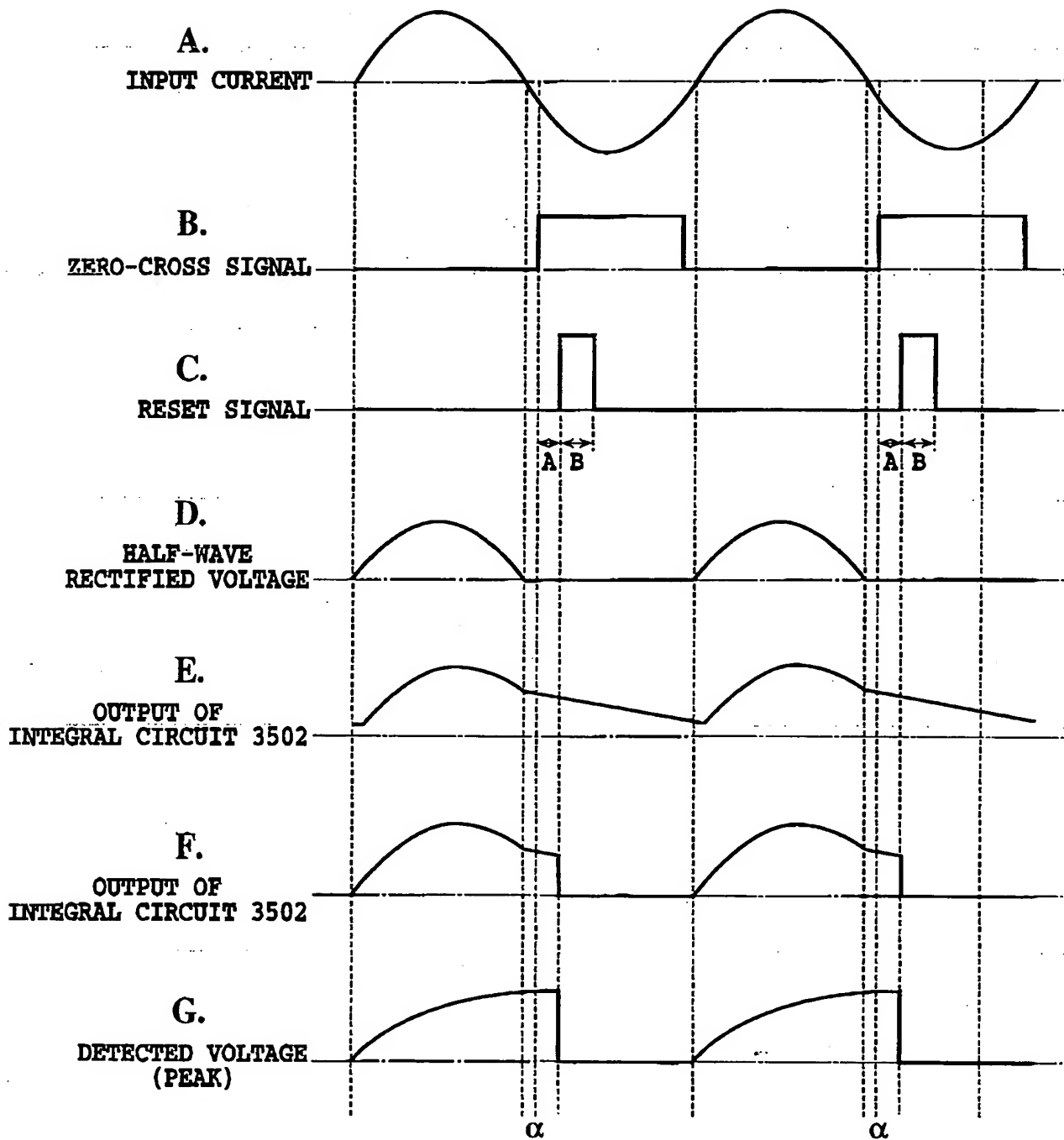


FIG.24

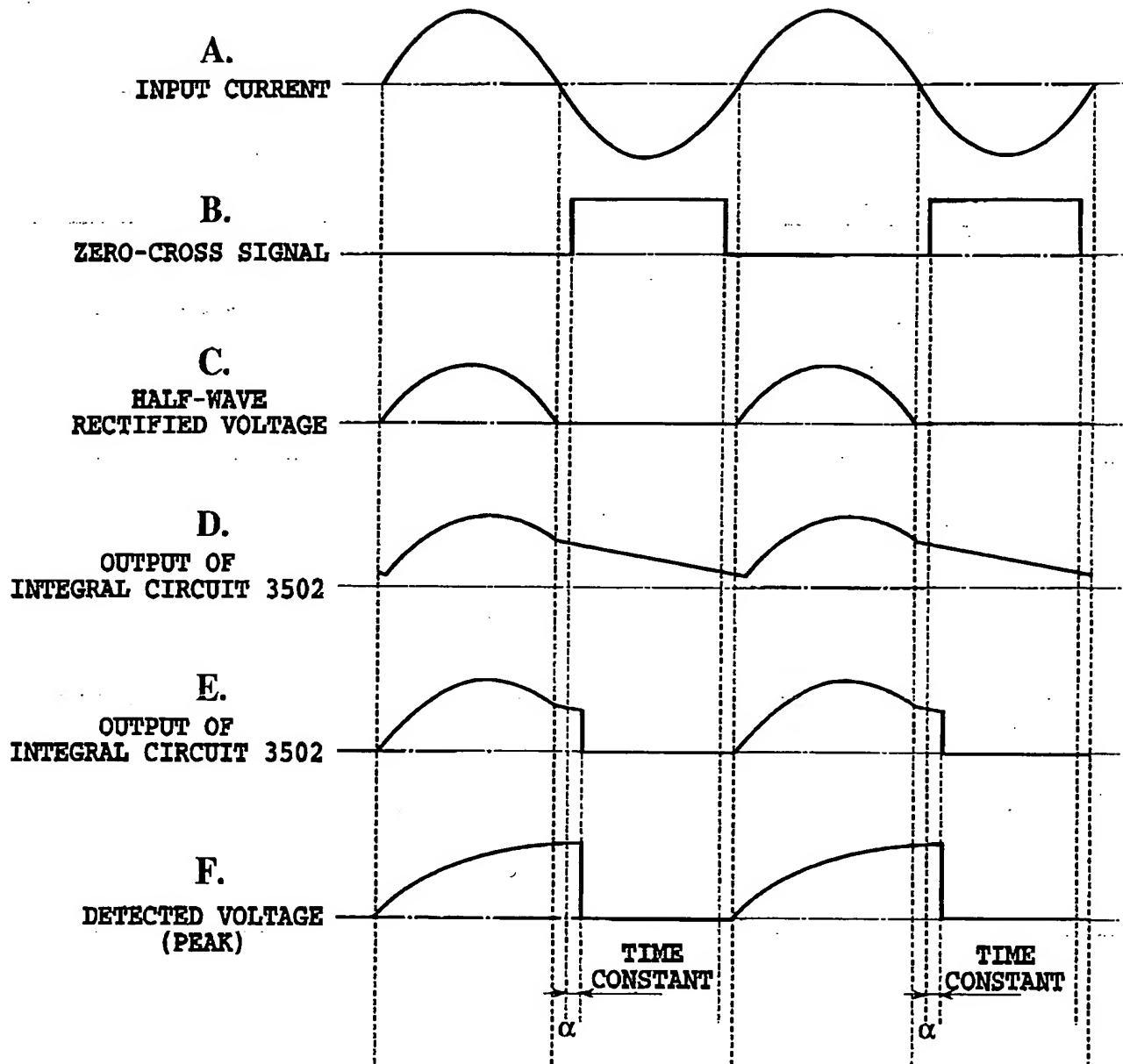


FIG.26